

ABSTRACT

ETCHING SOLUTION FOR ETCHING POROUS SILICON, ETCHING
METHOD USING THE ETCHING SOLUTION AND METHOD OF
PREPARING SEMICONDUCTOR MEMBER USING THE ETCHING SOLUTION

1

A method for preparing a semiconductor member
comprises:

5

forming a substrate having a non-porous
silicon monocrystalline layer and a porous silicon
layer;

10

bonding another substrate having a surface
made of an insulating material to the surface of the
monocrystalline layer; and

etching to remove the porous silicon layer by
immersing in an etching solution.

15

20

25

This Sheet Has Been Replaced

